



F	2018-7				
G	2019-11-30	2	RDSON 上限由原来的 22mR 改为 27mR		
H	2022-7-9	2 3	庞隆基申请 RDSON 上限由原来的 27mR 改为 35mR(典型值 18 改成 30), 更新曲线图		

Rev.H Jul.-2022



TO-220 P MOS
P-CHANNEL MOSFET in a TO-220 Plastic Package.



参

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Drain Current		$I_D(T_C=25^{\circ}\text{C})$	-50	A
Drain Current - Pulsed		I_{DM}	-200	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		$P_D(T_C=25^{\circ}\text{C})$	118	W
Single Pulsed Avalanche Energy		E_{AS}	250	mJ
Avalanche Current($L=0.5\text{mH}$)		I_{AS}	25	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	15	$^{\circ}\text{C/W}$
	Steady-State		60	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.1	

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Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}$ $I_D=-250\mu\text{A}$	-60	-68		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60\text{V}$ $V_{GS}=0\text{V}$			-1.0	μA
		$V_{DS}=-48\text{V}$ $T_C=150^{\circ}\text{C}$			-10	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$			± 0.1	μA
Gate Threshold Voltage	V_{th}	$V_{DS}=V_{GS}$ $I_D=-250\mu\text{A}$	-1	-1.6	-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10\text{V}$ $I_D=-20\text{A}$		30	35	$\text{m}\Omega$
	$R_{DS(on)}$	$V_{GS}=-4.5\text{V}$ $I_D=-10\text{A}$		40	45	$\text{m}\Omega$
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$ $I_S=-1\text{A}$			-1.2	V
Gate resistance	R_g			10		Ω
Input Capacitance	C_{iss}	$V_{DS}=-25\text{V}$ $V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		3200		pF
Output Capacitance	C_{oss}			800		pF



Parameter	<div>□</div> Symbol	Test Conditions	Min	Typ	参 Max	值 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-30V$ $R_L=1.5$ $R_{GEN}=3\ \Omega$		12		ns
Turn-On Rise Time	t_r			14.5		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			15		









